ABSTRACT

SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD OF SEMICONDUCTOR DEVICE

The present disclosure relates to a semiconductor device and manufacturing method of semiconductor device. A semiconductor device includes a gate structure including conductive layers and insulating layers alternately stacked with each other, channel structures passing through the gate structure and arranged in a first direction, a cutting structure extending in the first direction and passing through the channel structures, and a first slit structure passing through the gate structure and extending in a second direction crossing the first direction.

FIG. 1A